ABSTRACT

Disclosed are a method for manufacturing a semiconductor structure and a semiconductor structure. The method includes: providing a base substrate, where the base substrate is provided with active pillars and isolation layers spaced apart along a first direction, the active pillars and the isolation layers all extend along a second direction, the first direction is parallel to the surface of the base substrate, the second direction is parallel to the thickness direction of the base substrate, and the second direction is perpendicular to the first direction; removing a portion of each of the isolation layers to form a first groove; depositing a first dielectric layer at least on side walls of the first groove to form a second groove; forming a first metal layer, where the first metal layer directly covers at least the active pillars; performing a heat treatment to form conductive structures, where the first dielectric layer covers side walls of each of the conductive structures, the conductive structures extend along a third direction, and the third direction is perpendicular to the first direction and the second direction; and forming a second dielectric layer, where the second dielectric layer fills the second groove.

[FIG. 2I]